

Clean Portions of Specification

Heading at Page 1, line 6.

**2. DESCRIPTION OF PRIOR ART****BEST AVAILABLE COPY**

Paragraph at Page 1, Lines 7-15

Demands for high integration of semiconductor devices are constantly increasing and a new generation of 0.15  $\mu\text{m}$  gate lengths is now here. For such cases, it is known that improvement can be obtained in the properties of semiconductor devices by using Cu as wiring material, in place of conventional Al. That is, since Cu, has superior tolerance or resistance to EM (electro-migration), compared to Al, a low electrical resistance enables a reduction in signal delay or a decrease in level due to a wiring resistance. Therefore, it can be used under high current density. Specifically, by using this, the permissible current density can be released or enlarged up to three times, and the wiring width can also be made fine or minute.

Paragraph at Page 3, Lines 9-18

The present invention is based on what has been acknowledged above, and according to the present invention, there is provided a method for forming a coating film, comprising the following steps: applying a raw material of a low dielectric constant onto a surface of a plate-like material to be treated such as a semiconductor wafer or a glass substrate; reducing the oxygen concentration in the atmosphere surrounding the plate-like material to less than or equal to 1% before the surface temperature of the plate-like material to be treated rises to 200°C; thereafter heating the plate-like material to a temperature greater than or equal to 400°C while maintaining the oxygen concentration at less than or equal to 1%; and then maintaining the oxygen concentration in the atmosphere at less than or equal to 1% until the surface temperature of the plate-like material to be treated lowers to 200°C.

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Paragraph at Page 4, Lines 18-21

Although not shown in the figure, in this apparatus are provided a window portion, which can be freely opened or closed for moving the plate-like material to be treated W in and out, a gas supply conduit for supplying an atmospheric gas such as N<sub>2</sub> gas, and a gas discharge conduit for discharging the atmospheric gas from within the apparatus.

Paragraph at Page 11, Lines 2-10

In a case of using at least one kind selected among alkylene glycol dialkyl ether without using alcohol as a solvent, since alcohol corresponding to the alkoxy group is inevitably generated in the course of the hydrolysis of alkoxysilane, it is necessary to remove the generated alcohol from the reaction system. Specifically, it is necessary to remove the alcohol to be less than or equal to 15 weight % in this coating liquid, or more preferably, to be less than or equal to 8 weight %. If the alcohol exceeds 15 weight %, the H-Si group and the generated alcohol react with each other, an RO-Si group is generated, and thereby the cracking limit is deteriorated. In addition, gas is generated at the time of forming a coating film, and thereby the trouble mentioned above occurs.

**BEST AVAILABLE COPY**Marked-Up Copy of Amended Claims

4. (twice amended) A method for forming a coating film as defined in claim 1, wherein said [method is applied to a forming of] coating film is an interlayer insulation film and is further processed by a damascene method.

5. (amended) A method for forming a coating film as defined in claim 2, wherein said [method is applied to a forming of] coating film is an interlayer insulation film and is further processed by a damascene method.

6. (amended) A method for forming a coating film as defined in claim 3, wherein said [method is applied to a forming of] coating film is an interlayer insulation film and is further processed by a damascene method.